

Silicon NPN Power Transistors

BU526 BU526A

DESCRIPTION

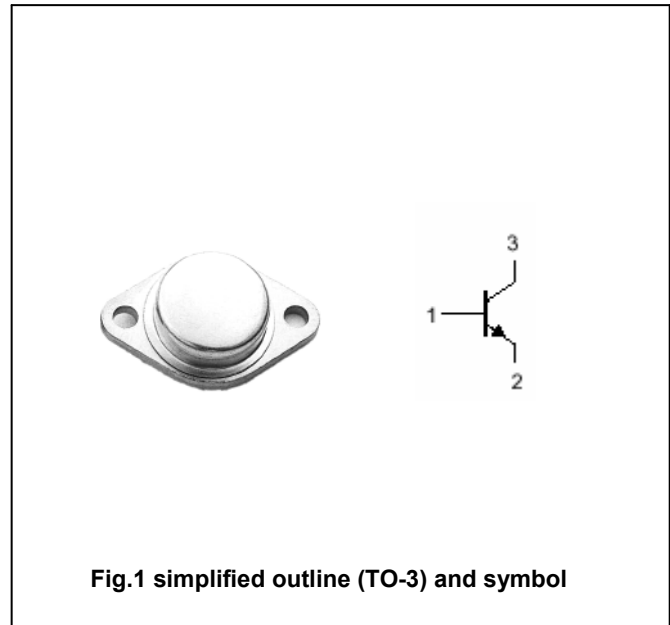
- With TO-3 package
- Short switching times.
- High dielectric strength.

APPLICATIONS

- For use in power supply units of TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	BU526	400	V
		BU526A	460	
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		10	A
P_T	Total power dissipation	$T_C = 25 \square$	86	W
T_j	Junction temperature		175	\square
T_{stg}	Storage temperature		-65~175	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-C}$	Thermal resistance junction to case	1.04	\square/W

Silicon NPN Power Transistors

BU526 BU526A

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50\text{mA}; I_B=0;$	400			V
			460			
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\text{mA}; I_C=0;$	7			V
$V_{CEsat-1}$	Collector-emitter saturation voltage	$I_C=5\text{A}; I_B=1\text{A}$			1.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	$I_C=8\text{A}; I_B=3\text{A}$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5\text{A}; I_B=1\text{A}$			1.6	V
I_{CBO}	Collector cut-off current	$V_{CB}=900\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7\text{V}; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	15		45	

Silicon NPN Power Transistors

BU526 BU526A

PACKAGE OUTLINE

